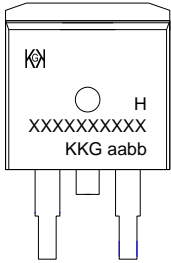


DESCRIPTION:

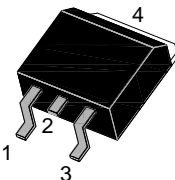
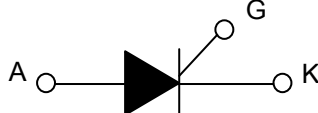
HBT151B series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

QUICK REFERENCE 【参考特性】

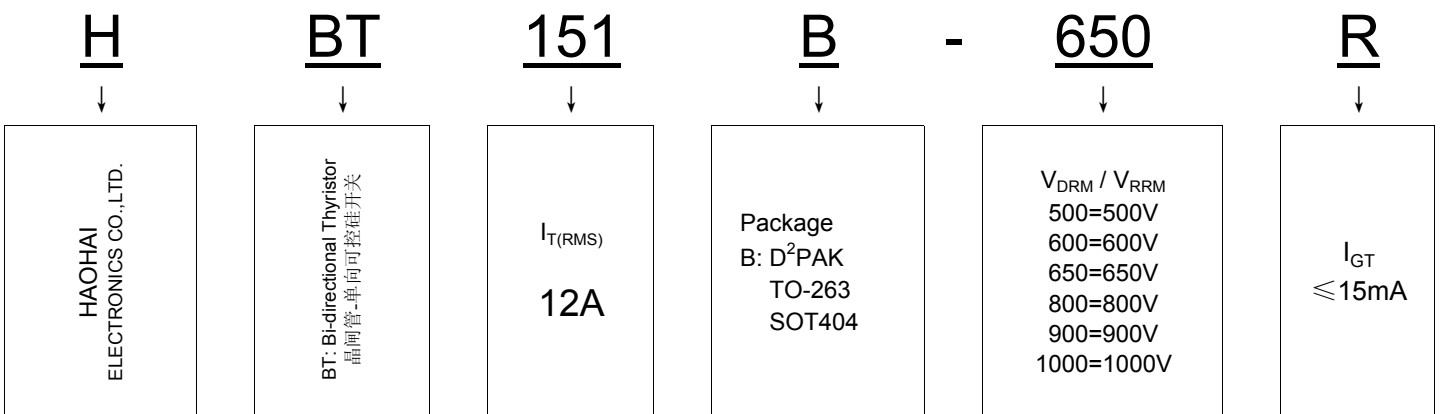
Part Number	Industry Part No	$I_{T(RMS)}$	$V_{DRM} / V_{RRM}$	$I_{GT}$	Package	Packing	Marking
HBT151B-500R	BT151B-500R	12A	500V	15mA	SMD D <sup>2</sup> PAK TO-263 SOT404	50Pcs/Tube 4Kpcs/Box 2.5Kpcs/Reel 每管50只 每盒4000只 或 每卷2500只 每盒5000只 2.1g / Pcs 每枚重量2.1克 每K重2.5克	
HBT151B-600R	BT151B-600R		600V				
HBT151B-650R	BT151B-650R		650V				
HBT151B-800R	BT151B-800R		800V				
HBT151B-900R	BT151B-900R		900V				
HBT151B-1000R	BT151B-1000R		1000V				
說明 Explain	①此規格為贴片封装、非絕緣型、單向可控硅，電流值可按客戶要求定制 ②常規品種以500V电压規格出貨，高壓規格600V品種以上批量交期6~8周 ③門極觸發電流IGT值可根據客戶要求細分至多個規格，單位mA (毫安)					元件標識可按 客戶指定要求	

PINNING: TO-263 (SOT404, D<sup>2</sup>PAK) 【表面貼TO-263片式封装】

【"B"表示贴片元件TO-263封装-載帶卷盤包裝】

Pin	Symbol	Description	Description	Practicality in Pin Arrange	Pin Polarity Circuit diagram
1	K	Cathode	陰極		
2	A	Anode	陽極		
3	G	Gate	門-控制極		
4	mb	mounting base	散熱片		

ORDERING INFORMATION



■ ABSOLUTE RATINGS (Limiting Values) 【额定值参数】

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current ( $T_C=100^\circ\text{C}$ )	12	A
$I_{TSM}$	Non repetitive surge peak on-state current ( $t_p=10\text{ms}$ )	120	
$I_{GM}$	Peak gate current	2	
$V_{DRM}$	Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	500~1000	V
$V_{RRM}$	Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		
$I^2t$	$I^2t$ value for fusing ( $t_p=10\text{ms}$ )	72	$\text{A}^2\text{S}$
$di_T/dt$	Repetitive rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )	50	$\text{A}/\mu\text{s}$
$P_{GM}$	Peak gate power	5	W
$P_{G(AV)}$	Average gate power dissipation	0.5	
$T_j$	Operating junction temperature range	-40~125	$^\circ\text{C}$
$T_{stg}$	Storage junction temperature range	-40~150	

■ ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12\text{V}, R_L=33\Omega$	--	4	15	mA
$I_L$	$I_G=1.2 I_{GT}$	--	12	40	
$I_H$	$I_T=500\text{mA}$	--	12	30	
$V_{GT}$	$V_D=12\text{V}, R_L=33\Omega$	--	0.75	1.5	V
$V_{GD}$	$V_D=V_{DRM}, T_j=125^\circ\text{C}, R_L=3.3\text{K}\Omega$	0.2	--	--	
$dV/dt$	$V_D=2/3V_{DRM}, \text{Gate Open}, T_j=125^\circ\text{C}$	200	400	--	$\text{V}/\mu\text{s}$

■ STATIC CHARACTERISTICS

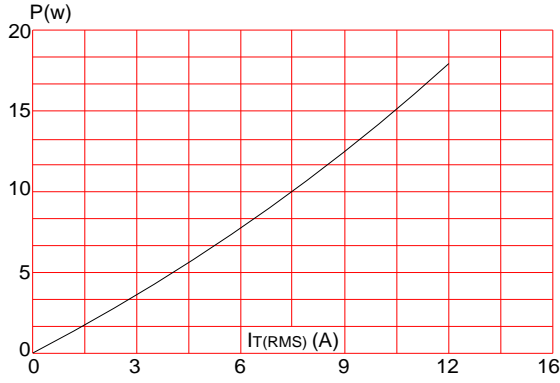
Symbol	Parameter	Value(MAX)	Unit
$V_{TM}$	$I_{TM}=23\text{A}, t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$ 1.7	V
$I_{DRM}$	$V_D=V_{DRM}, V_R=V_{RRM}$	$T_j=25^\circ\text{C}$ 10	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$ 1	mA

■ THERMAL RESISTANCES

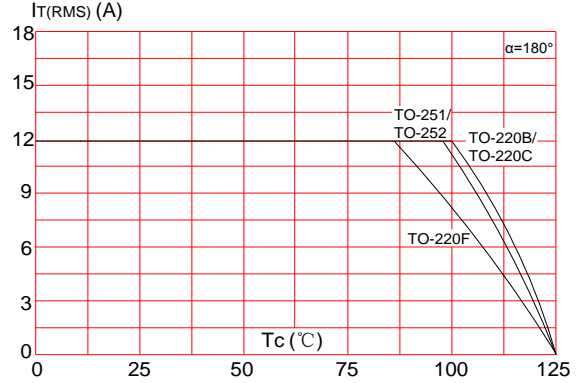
Symbol	Parameter	Value(MAX)	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	2.0	$^\circ\text{C}/\text{W}$

Electrical characteristics & Typical characteristics (电气特性与典型特征)

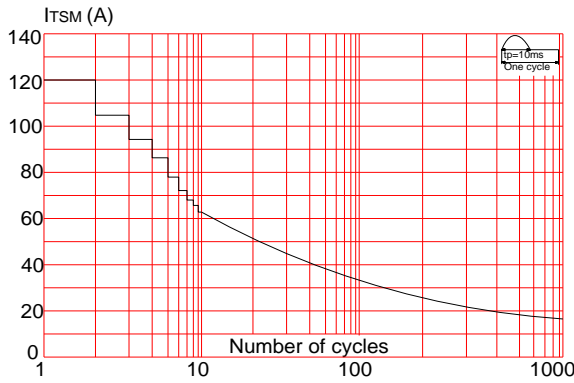
**FIG.1:** Maximum power dissipation versus RMS on-state current



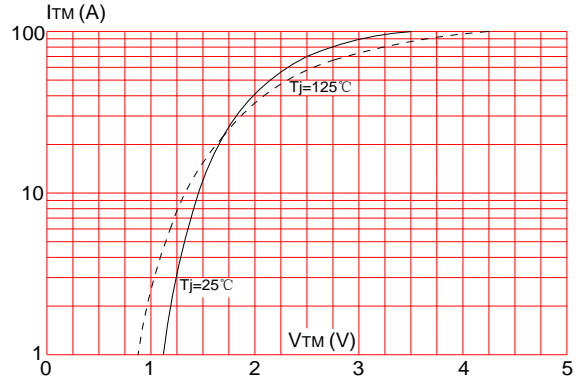
**FIG.2:** RMS on-state current versus case temperature



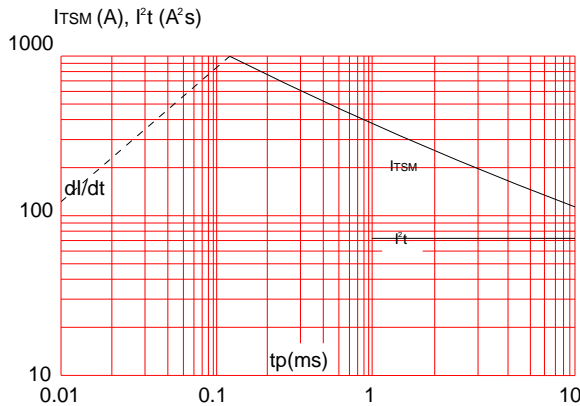
**FIG.3:** Surge peak on-state current versus number of cycles



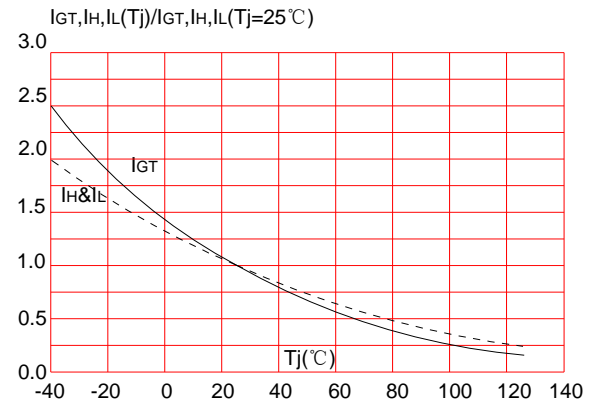
**FIG.4:** On-state characteristics (maximum values)



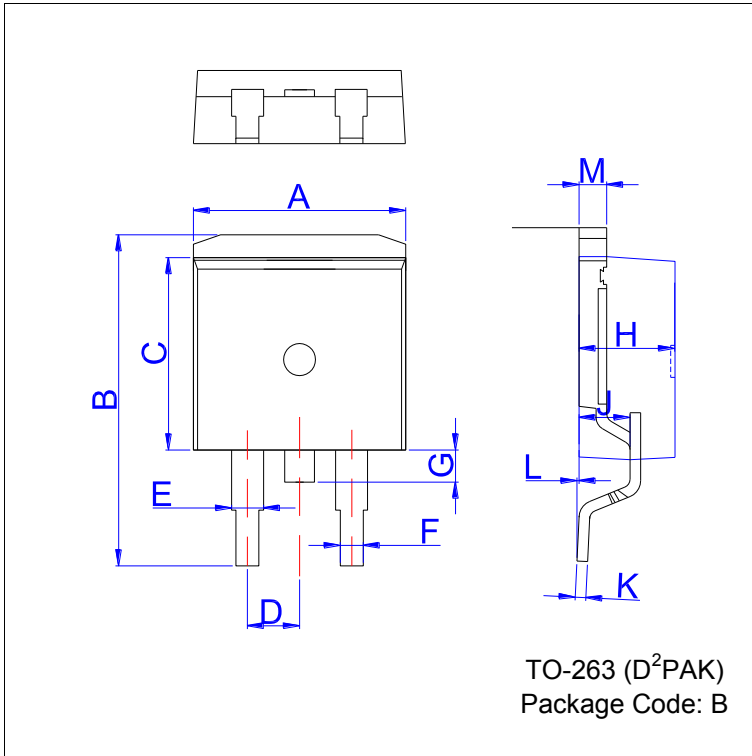
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2 t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

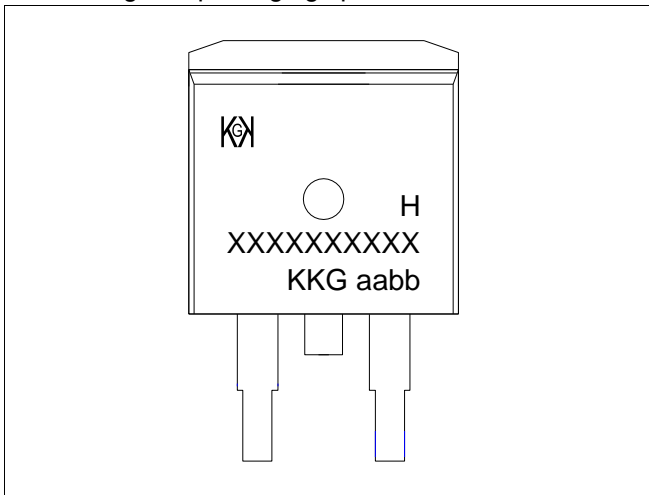


■ PACKAGE MECHANICAL DATA (mm & inch)  
TO-263 (SOT404 or D<sup>2</sup>PAK) 封装尺寸数据 (毫米与英寸对照)



REF	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	9.90	10.20	0.390	0.402
B	14.70	15.80	0.579	0.622
C	9.40	9.60	0.370	0.378
D	2.54		0.100	
E	1.20	1.40	0.047	0.055
F	0.75	0.85	0.029	0.033
G		1.75		0.069
H	4.40	4.70	0.173	0.185
J	2.30	2.70	0.091	0.106
K	0.38	0.55	0.015	0.022
L	0	0.25	0	0.010
M	1.25	1.35	0.049	0.053

■ Marking and packaging specifications



**打印标识**  
H: 浩海电子  
XXXXXXXXXX: 器件型号  
KKG: 注册商标  
aa: 出厂年份  
bb: 出厂自然周 (01~53)

**Marking**  
H: HAOHAI ELECTRONICS  
XXXXXXXXXX: Part Number  
KKG: Registered trademark  
aa: Factory Year  
bb: Factory natural Week (01~53)

**包装规格**  
TO-263: 条管装  
每管50只, 每盒4000只  
或 载带卷盘包装  
每卷2500只, 每盒5000只

**Packaging Specifications**  
50Pcs/Tub, 4Kpcs/BOX  
TO-263: Tape & Reel Packing  
2500Pcs/Reel, 5000Pcs/BOX

Manufacturers version information

2006-02-25, KKG™ Product Data-1.0

2010-07-25, KKG™ Product Data-1.1

2014-11-06, KKG™ Product Data-1.2



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